

Nucleation and Growth

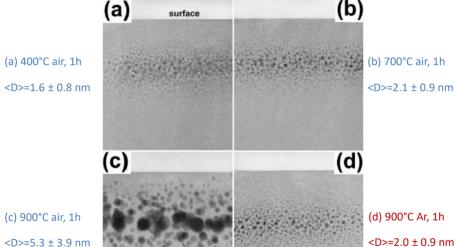
(Au NCs in SiO₂)

Energetics



NanoScience/ **NanoPhysics**





 $<D>=2.0 \pm 0.9 \text{ nm}$

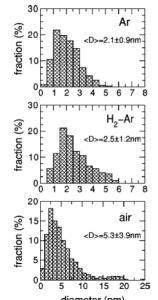
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Comparison among

900°C 1h

thermal annealings at

Au 190 keV, 3e16 ions/cm² in SiO₂



Ar (Inert)

H₂(4%)-Ar (Reducing)

 $<D>=2.1 \pm 0.9 \text{ nm}$

<D>=2.5 ± 1.2 nm

Air (Oxidizing)

 $<D>=5.3 \pm 3.9 \text{ nm}$

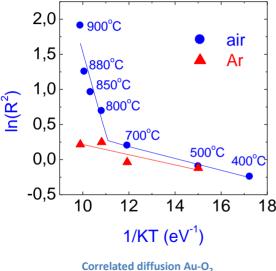
0 5 10 15 20 25 diameter (nm)



17



Au 190 keV, 3e16 ions/cm² in SiO₂



Activation energy of the process above 700°C (ΔE_{clu} = 1.2 eV) similar to the activation energy for the Oxygen diffusion (ΔE_{02} = 1.1-1.3 eV)

(Au diffusion in SiO_2 exhibits an activation energy ΔE_{Au} = 2.4 eV)

Correlated Diffusion (Onsager)

$$\begin{cases} \frac{\partial C_1}{\partial t} = D_{11} \frac{\partial^2 C_1}{\partial x^2} + D_{12} \frac{\partial^2 C_2}{\partial x^2} \\ \frac{\partial C_2}{\partial t} = D_{21} \frac{\partial^2 C_1}{\partial x^2} + D_{22} \frac{\partial^2 C_2}{\partial x^2} \end{cases}$$

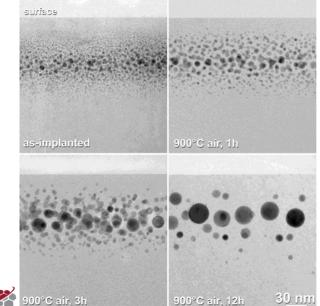


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(Au NCs in SiO₂)

Kinetics



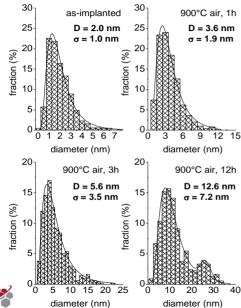


Thermal annealing in air at 900°C vs. time

(2001) 4249

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Au 190 keV, 3e16 ions/cm² in SiO₂

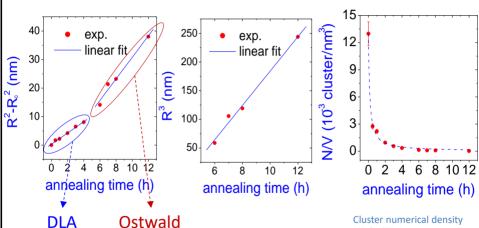


Thermal annealing in air at 900°C vs. time

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Au 190 keV, 3e16 ions/cm² in SiO₂

Growth Kinetics (900°C)



Change in the growth rate around 4 hrs of annealing



G. De Marchi, G. Mattei, P. Mazzoldi, C. Sada, A. Miotello, J. Appl. Phys. 92 (2001) 4249

(Nclu/V) decreases as a function of the anneling

time